



**AO6602**

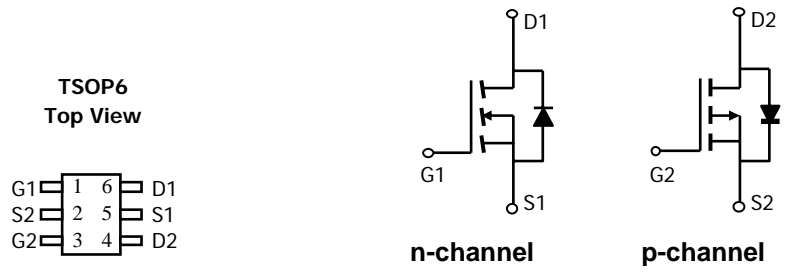
**Complementary Enhancement Mode Field Effect Transistor**

**General Description**

The AO6602 uses advanced trench technology to provide excellent  $R_{DS(ON)}$  and low gate charge. The complementary MOSFETs form a high-speed power inverter, suitable for a multitude of applications. *Standard Product AO6602 is Pb-free (meets ROHS & Sony 259 specifications). AO6602L is a Green Product ordering option. AO6602 and AO6602L are electrically identical.*

**Features**

n-channel	p-channel
$V_{DS} (V) = 30V$	-30V
$I_D = 3.1A (V_{GS} = 10V)$	-2.7A ( $V_{GS} = -10V$ )
$R_{DS(ON)}$	
$< 75m\Omega (V_{GS} = 10V) < 100m\Omega (V_{GS} = -10V)$	
$< 115m\Omega (V_{GS} = 4.5V) < 180m\Omega (V_{GS} = -4.5V)$	



**Absolute Maximum Ratings  $T_A=25^\circ C$  unless otherwise noted**

Parameter	Symbol	Max n-channel	Max p-channel	Units
Drain-Source Voltage	$V_{DS}$	30	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	$\pm 20$	V
Continuous Drain Current <sup>A</sup>	$I_D$	$T_A=25^\circ C$	3.1	-2.7
		$T_A=70^\circ C$	2.4	-2.1
Pulsed Drain Current <sup>B</sup>	$I_{DM}$	12	-12	A
Power Dissipation	$P_D$	$T_A=25^\circ C$	1.15	1.15
		$T_A=70^\circ C$	0.73	0.73
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	-55 to 150	$^\circ C$

**Thermal Characteristics: n-channel and p-channel**

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	78	110	$^\circ C/W$
Maximum Junction-to-Ambient <sup>A</sup>		106	150	$^\circ C/W$
Maximum Junction-to-Lead <sup>C</sup>	$R_{\theta JL}$	64	80	$^\circ C/W$

N-Channel Electrical Characteristics ( $T_J=25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$ , $V_{GS}=0\text{V}$	30			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=24\text{V}$ , $V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			1 5	$\mu\text{A}$
$I_{GSS}$	Gate-Body leakage current	$V_{DS}=0\text{V}$ , $V_{GS}=\pm 20\text{V}$			100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_D=250\mu\text{A}$	1	1.9	3	V
$I_{D(ON)}$	On state drain current	$V_{GS}=10\text{V}$ , $V_{DS}=5\text{V}$	10			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}$ , $I_D=3.1\text{A}$ $T_J=125^\circ\text{C}$		54 78	75	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}$ , $I_D=2\text{A}$		88	115	$\text{m}\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS}=5\text{V}$ , $I_D=3.1\text{A}$		4.5		S
$V_{SD}$	Diode Forward Voltage	$I_S=1\text{A}$		0.79	1	V
$I_S$	Maximum Body-Diode Continuous Current				2.5	A
<b>DYNAMIC PARAMETERS</b>						
$C_{iss}$	Input Capacitance	$V_{GS}=0\text{V}$ , $V_{DS}=15\text{V}$ , $f=1\text{MHz}$		200	240	pF
$C_{oss}$	Output Capacitance			40		pF
$C_{riss}$	Reverse Transfer Capacitance			20		pF
$R_g$	Gate resistance	$V_{GS}=0\text{V}$ , $V_{DS}=0\text{V}$ , $f=1\text{MHz}$		2.3	3	$\Omega$
<b>SWITCHING PARAMETERS</b>						
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS}=10\text{V}$ , $V_{DS}=15\text{V}$ , $I_D=3.1\text{A}$		6.5	8.5	nC
$Q_g(4.5\text{V})$	Total Gate Charge			3.1	4	nC
$Q_{gs}$	Gate Source Charge			1.2		nC
$Q_{gd}$	Gate Drain Charge			1.6		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=10\text{V}$ , $V_{DS}=15\text{V}$ , $R_L=4.7\Omega$ , $R_{GEN}=3\Omega$		3.3		ns
$t_r$	Turn-On Rise Time			2.5		ns
$t_{D(off)}$	Turn-Off DelayTime			13.2		ns
$t_f$	Turn-Off Fall Time			1.7		ns
$t_{rr}$	Body Diode Reverse Recovery Time	$I_F=3.1\text{A}$ , $di/dt=100\text{A}/\mu\text{s}$		9.4	12	ns
$Q_{rr}$	Body Diode Reverse Recovery Charge	$I_F=3.1\text{A}$ , $di/dt=100\text{A}/\mu\text{s}$		3.5		nC

A: The value of  $R_{\theta JA}$  is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The value in any given application depends on the user's specific board design. The current rating is based on the  $t_s \leq 10\text{s}$  thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C. The  $R_{\theta JA}$  is the sum of the thermal impedance from junction to lead  $R_{\theta JL}$  and lead to ambient.

D. The static characteristics in Figures 1 to 6,12,14 are obtained using 80 $\mu\text{s}$  pulses, duty cycle 0.5% max.

E. These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The SOA curve provides a single pulse rating.

Rev 3 : June 2005

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N-Channel Electrical Characteristics ( $T_J=25^\circ\text{C}$  unless otherwise noted)

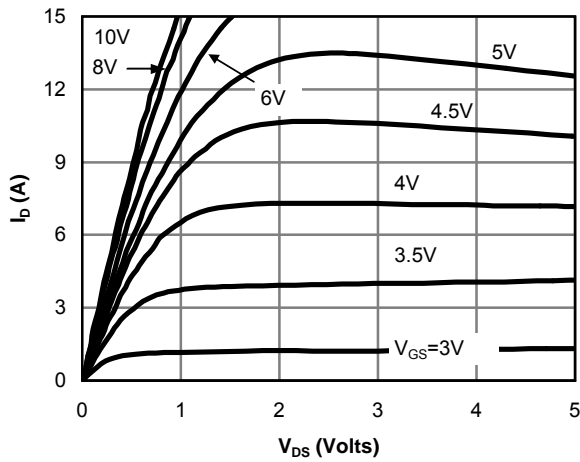


Fig 1: On-Region Characteristics

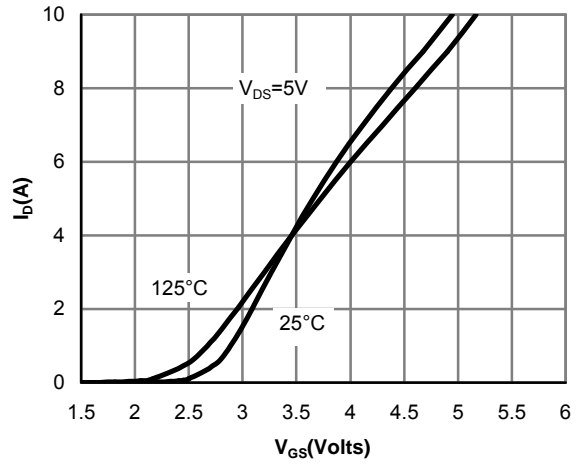


Figure 2: Transfer Characteristics

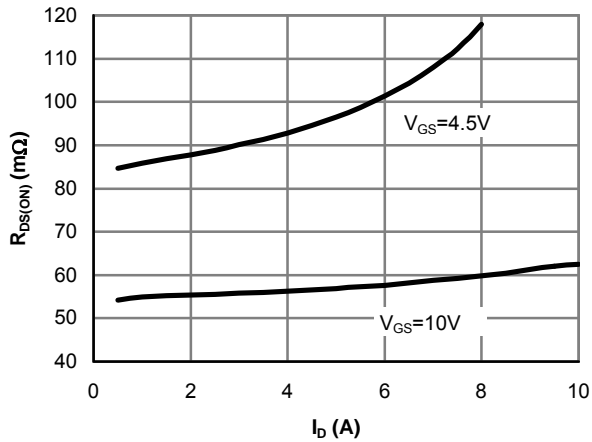


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

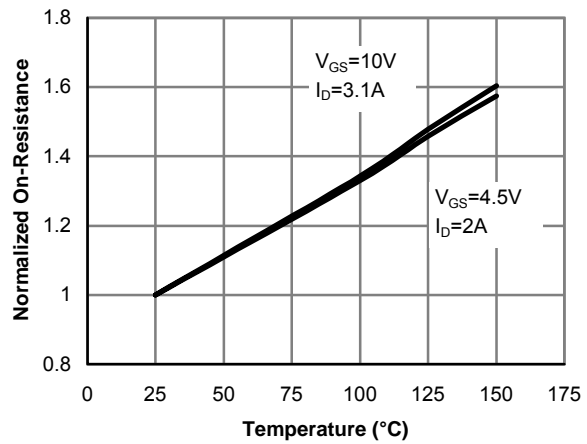


Figure 4: On-Resistance vs. Junction Temperature

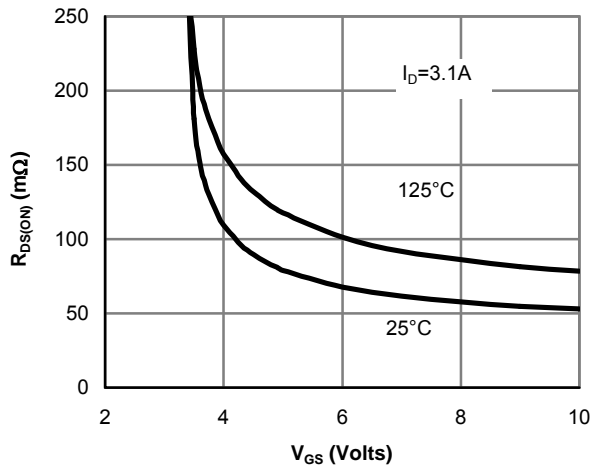


Figure 5: On-Resistance vs. Gate-Source Voltage

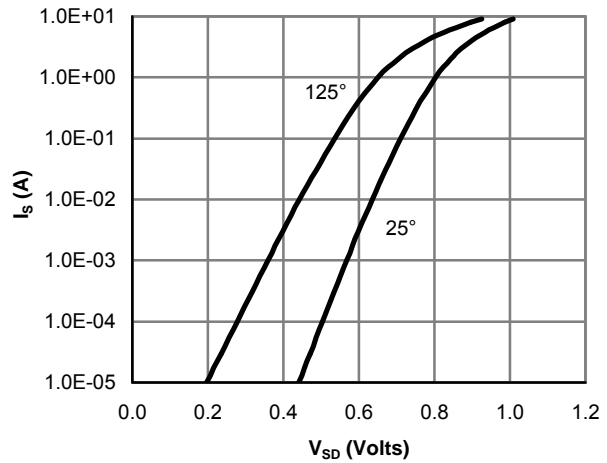


Figure 6: Body-Diode Characteristics

N-Channel Electrical Characteristics ( $T_J=25^\circ\text{C}$  unless otherwise noted)

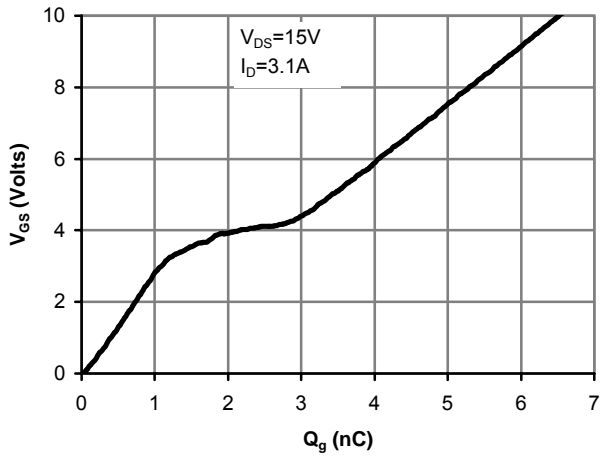


Figure 7: Gate-Charge Characteristics

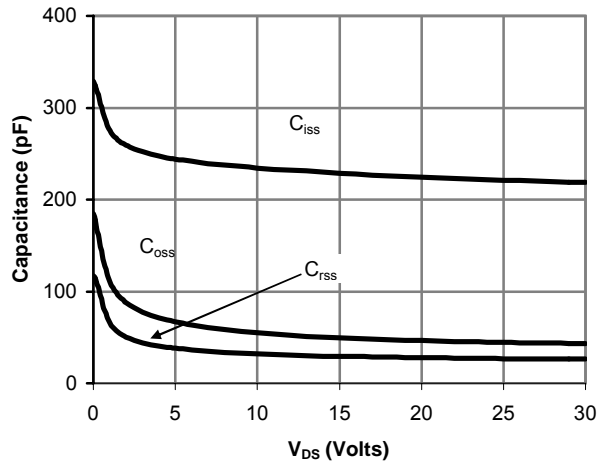


Figure 8: Capacitance Characteristics

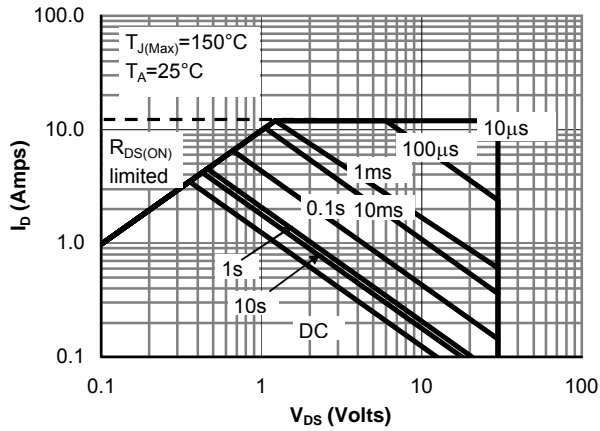


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

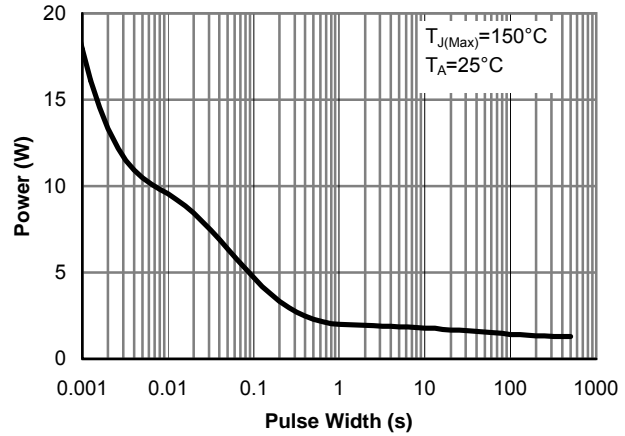


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

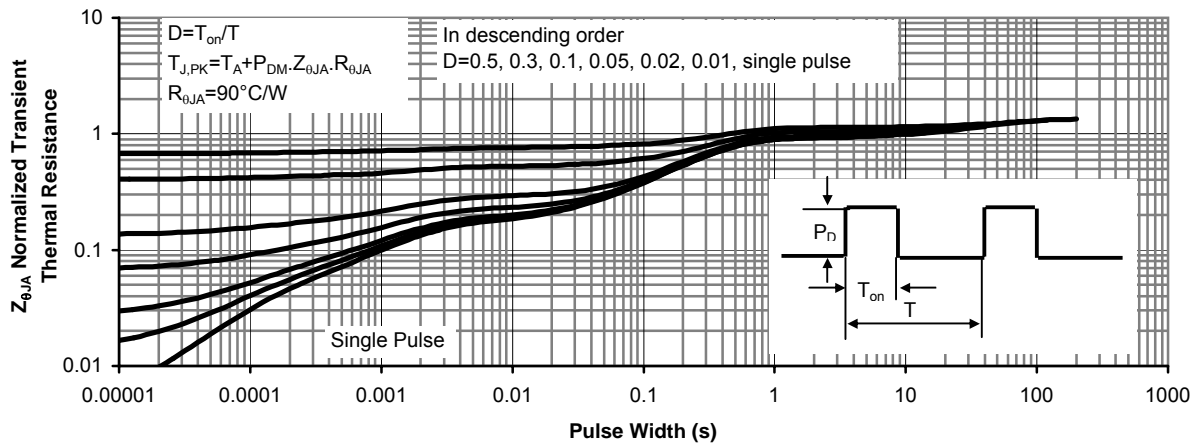


Figure 11: Normalized Maximum Transient Thermal Impedance

P-Channel Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> =-250μA, V <sub>GS</sub> =0V	-30			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V T <sub>J</sub> =55°C			-1 -5	μA
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-1	-1.9	-3	V
I <sub>D(ON)</sub>	On state drain current	V <sub>GS</sub> =-4.5V, V <sub>DS</sub> =-5V	-5			A
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =-10V, I <sub>D</sub> =-2.7A T <sub>J</sub> =125°C		77 110	100	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-2A		130	180	mΩ
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =-5V, I <sub>D</sub> =-2.7A		4.1		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =-1A, V <sub>GS</sub> =0V		-0.81	-1	V
I <sub>S</sub>	Maximum Body-Diode Continuous Current				-2	A
<b>DYNAMIC PARAMETERS</b>						
C <sub>iss</sub>	Input Capacitance			260	312	pF
C <sub>oss</sub>	Output Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =-15V, f=1MHz		55		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			44		pF
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz		4.3	5	Ω
<b>SWITCHING PARAMETERS</b>						
Q <sub>g(10)</sub>	Total Gate Charge(10V)			5.8	7	nC
Q <sub>g(4.5)</sub>	Total Gate Charge(4.5V)	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-15V, I <sub>D</sub> =-2.7A		3	4	nC
Q <sub>gs</sub>	Gate Source Charge			0.78		nC
Q <sub>gd</sub>	Gate Drain Charge			1.6		nC
t <sub>D(on)</sub>	Turn-On DelayTime			7		ns
t <sub>r</sub>	Turn-On Rise Time	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-15V, R <sub>L</sub> =5.6Ω,		6		ns
t <sub>D(off)</sub>	Turn-Off DelayTime	R <sub>GEN</sub> =3Ω		15		ns
t <sub>f</sub>	Turn-Off Fall Time			7.5		ns
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =-2.7A, dI/dt=100A/μs		12.5	15	ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =-2.7A, dI/dt=100A/μs		5.5		nC

A: The value of R<sub>θJA</sub> is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The value in any a given application depends on the user's specific board design. The current rating is based on the ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C. The R<sub>θJA</sub> is the sum of the thermal impedance from junction to lead R<sub>θJL</sub> and lead to ambient.

D. The static characteristics in Figures 1 to 6,12,14 are obtained using 80μs pulses, duty cycle 0.5% max.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS: P-CHANNEL

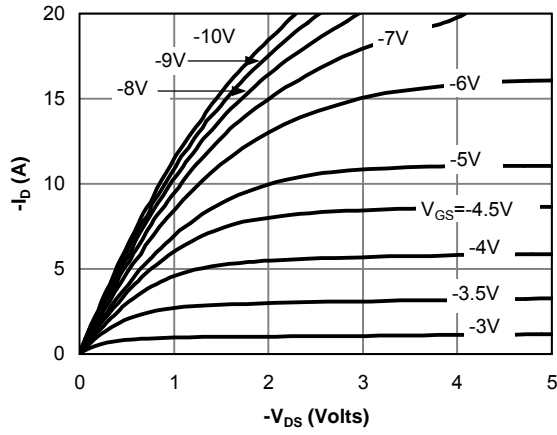


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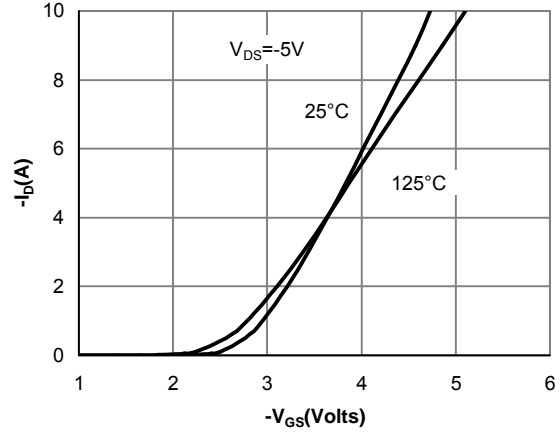


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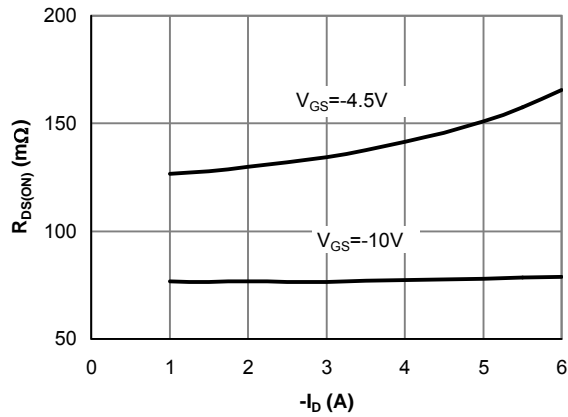


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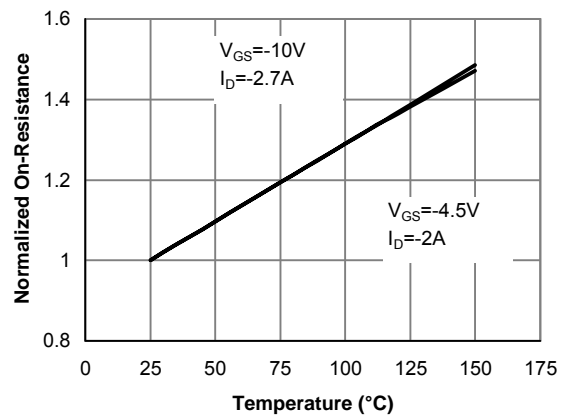


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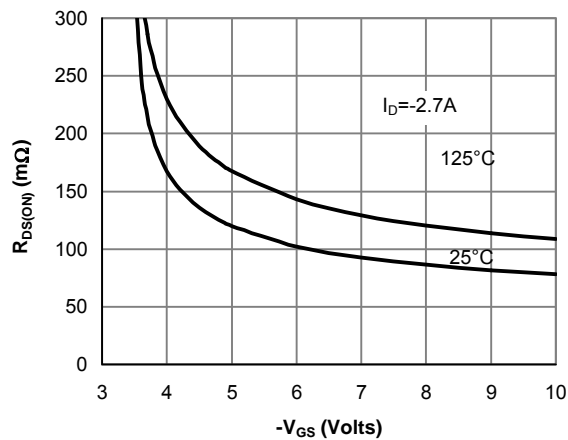


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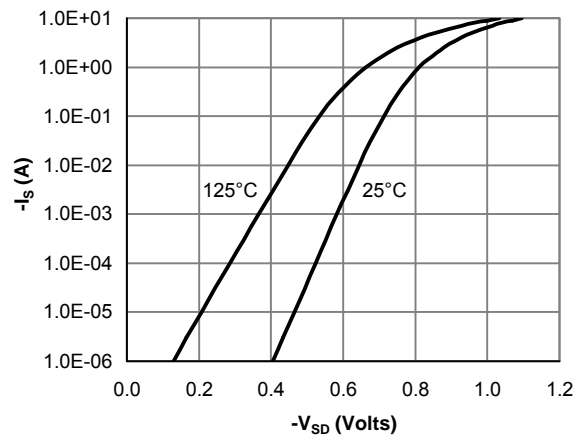


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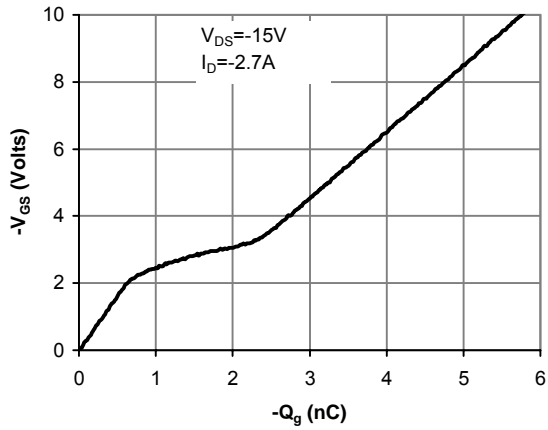


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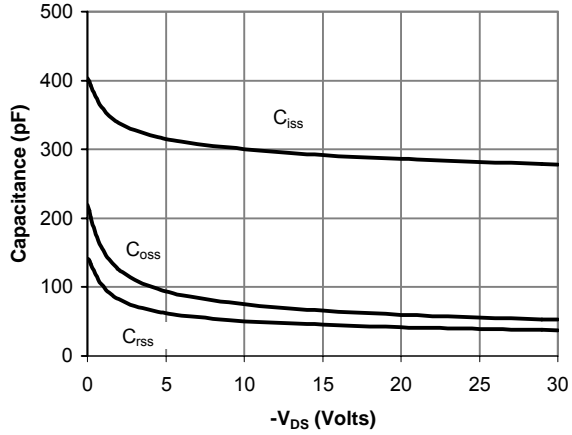


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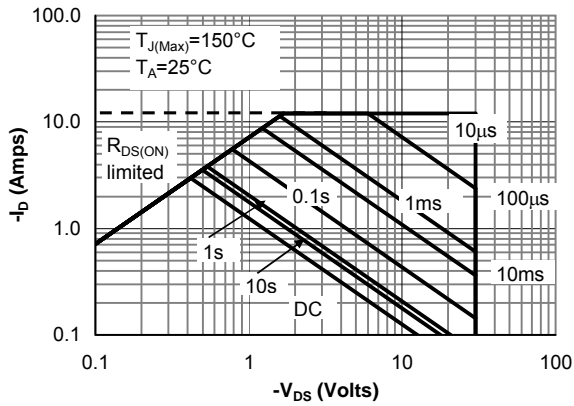


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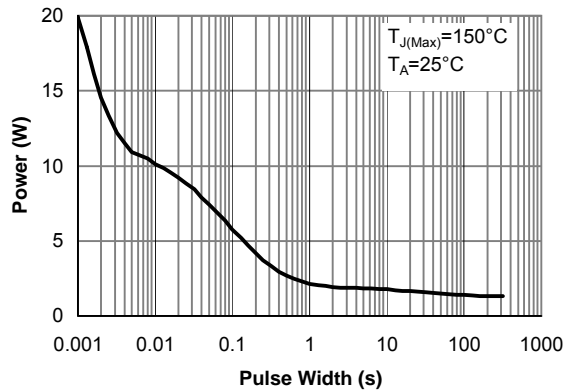


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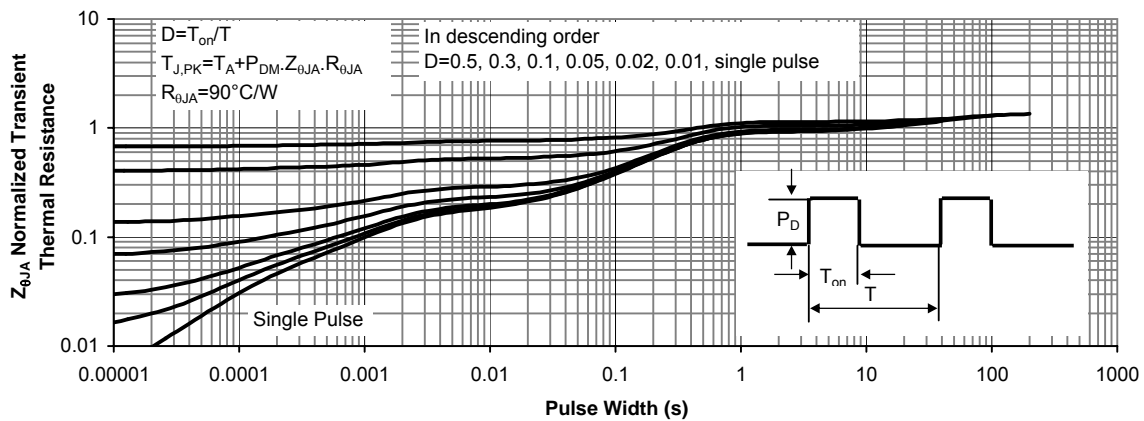


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